

Silicon PNP Power Transistors

2SA914

DESCRIPTION

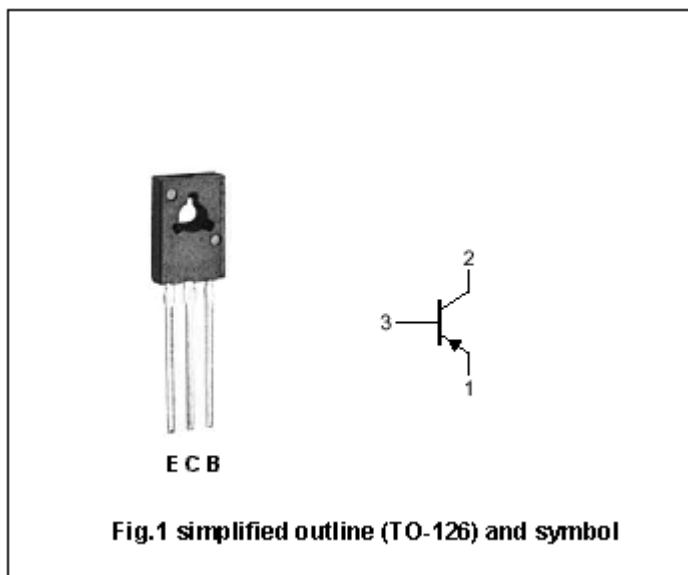
- With TO-126 package
- Complement to type 2SC1953
- Good linearity of h_{FE}
- High V_{CEO}

APPLICATIONS

- For audio frequency power pre-amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-50	mA
I_{CM}	Collector current-Peak		-100	mA
P_C	Collector power dissipation		1.2	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-0.1mA; I_B=0$	-150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-10\mu A; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-30mA; I_B=-3mA$			-1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-100V; I_E=0$			-1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-1	μA
h_{FE}	DC current gain	$I_C=-10mA; V_{CE}=-5V$	90		450	
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-10V; f=1MHz$			5	pF
f_T	Transition frequency	$I_C=10mA; V_{CB}=-10V$	70			MHz

◆ h_{FE} Classifications

Q	R	S	T
90-155	130-220	185-330	260-450

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PACKAGE OUTLINE

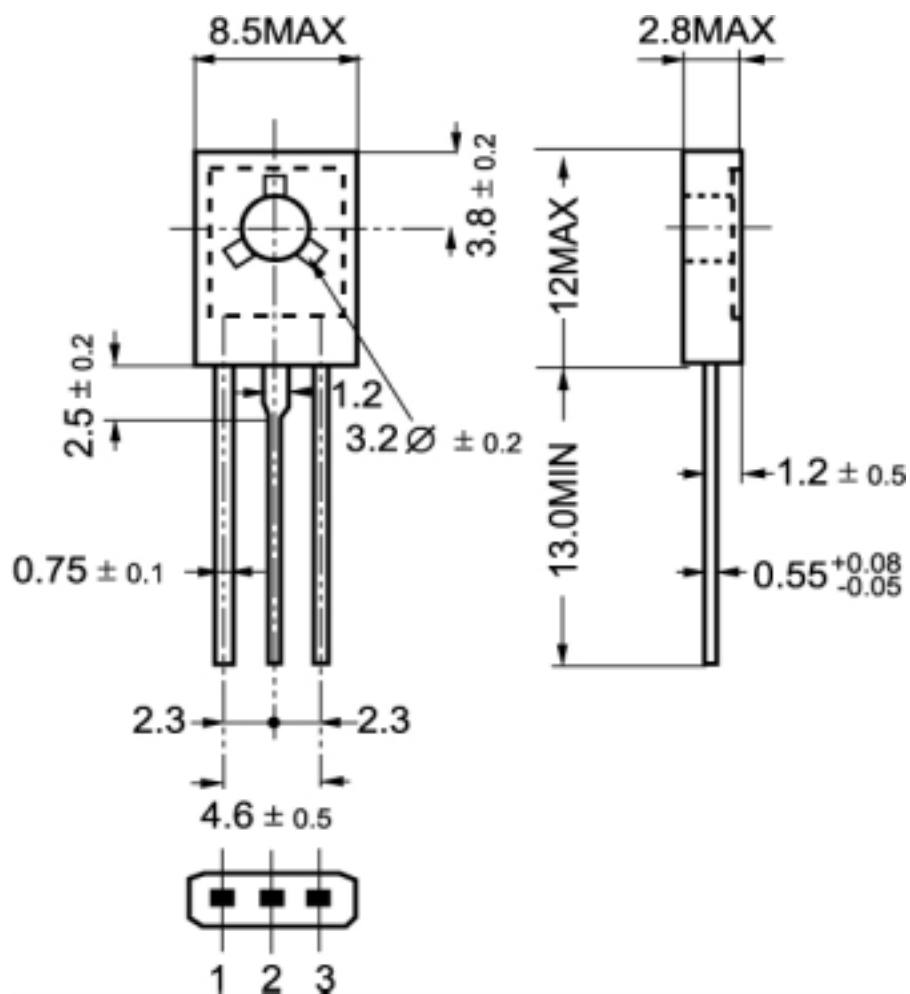


Fig.2 Outline dimensions